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BC337

Silicon NPN Transistor Audio Amplifier, Switch

Features:

- Suitable for AF-Driver Stages and Low Power Output Stages

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector-Emitter Voltage, V_{CES}	50V
Collector-Emitter Voltage, V_{CEO}	45V
Emitter-Base Voltage, V_{EBO}	5V
Continuous Collector Current, I_C	800mA
(Collector Power Dissipation), P_D	625mW
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	45	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C = 0.1\text{mA}, V_{BE} = 0$	50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 0.1\text{mA}, I_C = 0$	5	-	-	V
Collector Cutoff Current	I_{CES}	$V_{CE} = 45\text{V}, I_B = 0$	-	2	100	nA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{V}, I_C = 100\text{mA}$	100	-	630	
		$V_{CE} = 1\text{V}, I_C = 300\text{mA}$	60	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	0.7	V
Base-Emitter ON Voltage	$V_{BE(on)}$	$V_{CE} = 1\text{V}, I_C = 300\text{mA}$	-	-	1.2	V
Current Gain-Bandwidth Product	f_T	$I_C = 10\text{mA}, V_{CE} = 5\text{V}, f = 50\text{MHz}$	-	100	-	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	-	12	-	pF

